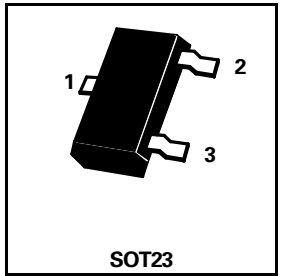
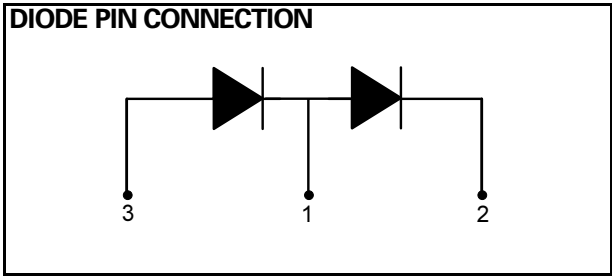


# SOT23 SILICON PLANAR LOW LEAKAGE SERIES DIODE PAIR

ISSUE 2 – SEPTEMBER 1995 ♻

FLLD261



PART MARKING DETAIL – P8A

## ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Repetitive Peak Reverse Voltage	$V_{RRM}$	100	V
Average Rectified Forward Current	$I_{F(AV)}$	250	mA
Non-Repetitive Peak Forward Current (t=1μs)	$I_{FSM}$	3.0	A
Power Dissipation at $T_{amb} = 25^{\circ}C$	$P_{tot}$	330	mW
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^{\circ}C$

## ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Reverse Current	$I_R$		5 5	nA μA	$V_{RRM}=100V$ $V_{RRM}=100V, T_{amb}=150^{\circ}C$
Reverse Recovery Time*	$t_{rr}$		400	ns	$I_F = I_R = 50 - 400mA$
Forward Recovery Time	$t_{fr}$		10	ns	$I_F = 10mA$
Diode Capacitance	$C_d$		4	pF	$V_R = 1V, f = 1MHz$
Forward Overshoot Voltage	$V_{fr}$		Typ 0.9	V	$I_F = 10mA,$ Rise time=5ns ±20%
Forward Voltage	$V_F$		1.4	V	$I_F = -200mA$

\*Time for  $I_R$  to recover to 10% of  $I_R$  peak  
For typical characteristics graphs see FLLD263 datasheet.

**FLLD258**  
**FLLD261**  
**FLLD263**

**TYPICAL CHARACTERISTICS**

